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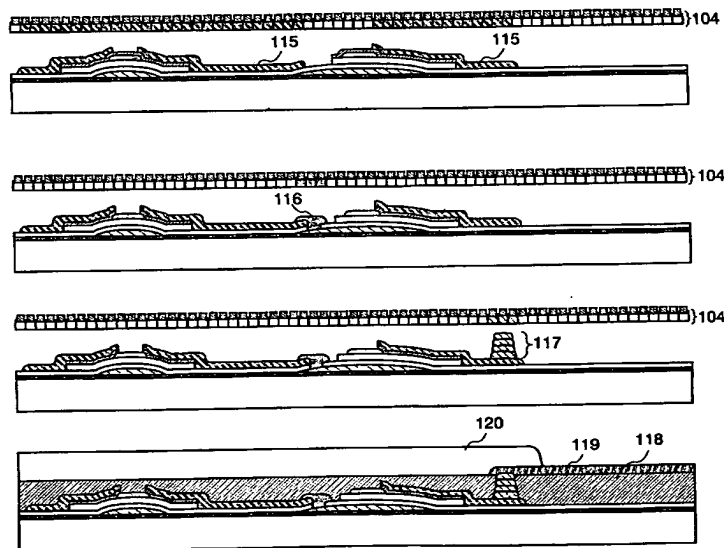
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(54) Title: DISPLAY DEVICE AND METHOD FOR FABRICATING THE SAME



(57) Abstract: It is an object of the invention to provide a display device which can be manufactured by a simplified manufacturing process by which the efficiency in the use of material is improved. It is a further object of the invention to provide a manufacturing method of the display device. It is another object of the invention to provide a fabrication technology for improving adhesion of a pattern. In view of the above problems, according to the present invention, a pattern is formed by a droplet discharge method. Particularly in the invention, base pretreatment is performed before/after a pattern is formed by a droplet discharge method. As a result of such base pretreatment, adhesion of a pattern can be improved, and the pattern may be made finer.



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